IN THE CLAIMS:

Claims 1-13 (Canceled)

Claim 14 (currently amended): A method of fabricating a semiconductor package for three-dimensional mounting, comprising:

(a) <u>providing a substrate</u>, placing semiconductor chip on an upper surface of a substrate, said substrate having the

an upper surface of the substrate including a first region and a second region, the first region including on which a first an upper metal pattern [[is]] formed thereon and the second region including at least one registration mark.

a lower surface of the substrate including on which a second lower metal pattern [[is]] formed thereon, said first upper metal pattern and second said lower metal pattern being electrically connected to each other through said substrate;

- (b) providing a semiconductor chip;
- (c) placing said semiconductor chip on the upper surface of said substrate within the first region;
- (d) electrically connecting the semiconductor chip and the first upper metal pattern to each other;
- [[(c)]] (e) sealing the semiconductor chip and the first upper metal pattern with sealing resin, the sealing resin covering the first region but not the second region, whereby the registration mark is not covered by the resin; and
- [[(d)]] (f) forming, in the first region and through the sealing resin, a through hole which reaches the first upper metal pattern by using the registration mark to align the through hole to the upper metal pattern; [[,]] and
- (g) forming a wire inside the through hole to electrically connect to the first upper metal pattern.

Claim 15 (currently amended): [[A]] <u>The</u> method according to claim 14, wherein the through hole is formed by irradiating a laser beam onto a predetermined position of the surface of the sealing resin.

Claim 16 (currently amended): A method of fabricating a semiconductor package for three-dimensional mounting, comprising:

- (a) preparing a substrate <u>having an upper surface and a lower surface</u>, the upper surface of the substrate including a first region and a second region, the second region including at least one registration mark;
 - (b) forming a first an upper metal pattern on an upper surface of the substrate;
 - (c) forming a second lower metal pattern on a lower surface of the substrate;
- (d) electrically connecting the first upper metal pattern and the second lower metal pattern to each other;
 - (e) placing a semiconductor chip on the upper surface of the substrate;
- (f) electrically connecting the semiconductor chip and the first upper metal pattern to each other;
- (g) sealing the semiconductor chip and the first upper metal pattern with sealing resin, the sealing resin covering the first region but not the second region, whereby the registration mark is not covered by the resin;
- (h) forming, in the first region and through the sealing resin, a through hole extending from the surface of the sealing resin to the first upper metal pattern by using the registration mark to align the through hole to the upper metal pattern; and
 - (i) forming a wire inside the through hole.

Claim 17 (currently amended): [[A]] The method according to claim 16, wherein the through hole is formed by irradiating a laser beam onto a predetermined position of the surface of the sealing resin.

Claim 18 (currently amended): [[A]] The method according to claim 14, further comprising:

- (a) disposing a second substrate on the sealing resin after forming the wire inside the through hole; and
- (b) electrically connecting the wire formed inside the through hole and a third metal pattern formed on the second substrate to each other.

Claim 19 (currently amended): [[A]] The method according to claim 14, wherein said placing a semiconductor chip includes placing a plurality of semiconductor chips on the upper surface of the substrate, the method further comprising:

separating the plurality of semiconductor chips from each other to obtain a plurality of semiconductor packages after forming the wire inside the through hole.

Claim 20 (currently amended): [[A]] <u>The</u> method according to claim 14, further comprising:

- (a) forming a fourth wire on the surface of the sealing resin after forming the wire inside the through hole, the fourth wire being electrically connected to one end of the wire;
 - (b) forming an insulating layer on the fourth wire; and
- (c) forming a third electrode which is electrically connected to the fourth wire and exposed from the insulating layer.

Claim 21 (currently amended): [[A]] <u>The</u> method according to claim 16, further comprising:

- (a) disposing a second substrate on the sealing resin after forming the wire inside the through hole; and
- (b) electrically connecting the wire formed inside the through hole and a third metal pattern formed on the second substrate to each other.

Claim 22 (currently amended): [[A]] <u>The</u> method according to claim 16, wherein said placing a semiconductor chip includes placing a plurality of semiconductor chips on the upper surface of the substrate, the method further comprising:

separating the plurality of semiconductor chips from each other to obtain a plurality of semiconductor packages after forming the wire inside the through hole.

Claim 23 (currently amended): [[A]] <u>The</u> method according to claim 16, further comprising:

- (a) forming a fourth wire on the surface of the sealing resin after forming the wire inside the through hole, the fourth wire being electrically connected to one end of the wire;
 - (b) forming an insulating layer on the fourth wire; and
- (c) forming a third electrode which is electrically connected to the fourth wire and exposed from the insulating layer.

Claim 24 (new): The method according to claim 14, comprising forming the registration mark along with the upper metal pattern.

Claim 25 (new): The method according to claim 16, comprising forming the registration mark along with the upper metal pattern.

Claim 26 (new): The method according to claim 14,

wherein the step of placing said semiconductor chip on the upper surface of said substrate within the first region includes placing a plurality of the semiconductor chip on a single substrate;

wherein the plural semiconductor chips are deployed on the substrate in a rectangular array within the first region; and

wherein the step of providing the substrate includes forming the registration mark within the second region at a corner of the array.

Claim 27 (new): The method according to claim 16,

wherein the step of placing said semiconductor chip on the upper surface of said substrate within the first region includes placing a plurality of the semiconductor chip on a single substrate;

wherein the plural semiconductor chips are deployed on the substrate in a rectangular array within the first region; and

wherein the step of providing the substrate includes forming the registration mark within the second region at a corner of the array.